

1-Line Ultra Capacitance Bi-directional TVS Diode

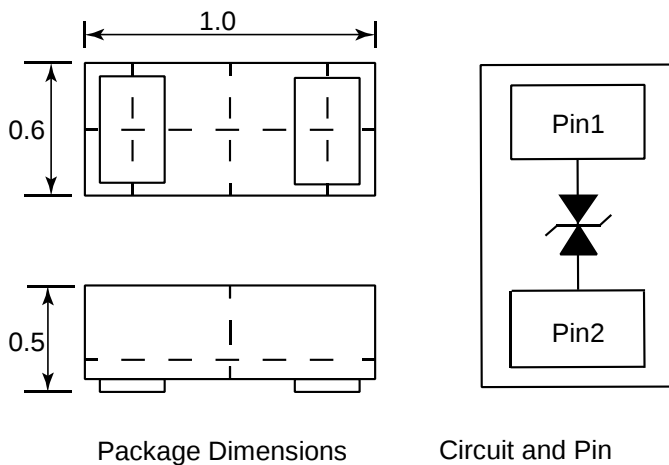
Description

The PESDR1821P1 is a bi-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR1821P1 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 25\text{kV}$ air and $\pm 25\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR1821P1 an ideal choice to protect cell phone, digital visual interfaces and other high speed ports.

Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.3pF typical
- Operating voltage: 18V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 25\text{kV}$
 - Contact discharge: $\pm 25\text{kV}$
- RoHS Compliant

Dimensions and Pin Configuration



Mechanical Characteristics

- Package: DFN1006-2 (1.0x0.6x0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Antenna
- Cellular Handsets and Accessories
- Display Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports
- Digital Camera

Marking Information



R18 = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDR1821P1	10000/Tape & Reel	7 inch

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

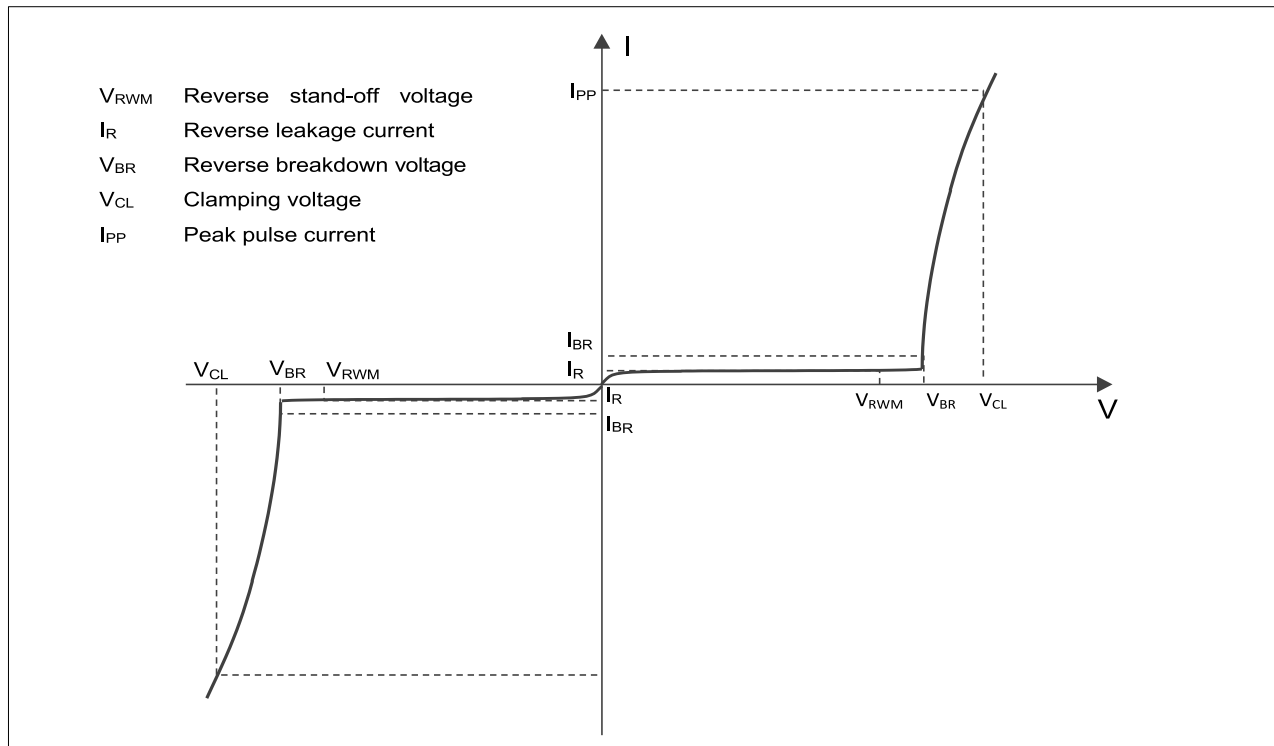
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	62	W
Peak Pulse Current (8/20μs)	I _{PP}	2	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±25	kV
ESD per IEC 61000-4-2 (Contact)		±25	
Lead temperature	T _L	260	°C
Junction Temperature	T _J	125	°C
Operating Temperature Range	T _{OP}	-40 ~ +125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			18	V	
Breakdown Voltage	V _{BR}	19.5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 18V
Clamping Voltage	V _C			26	V	I _{PP} = 1A (8/20μs pulse)
Clamping Voltage	V _C			31	V	I _{PP} = 2A (8/20μs pulse)
Junction Capacitance	C _J		0.3		pF	V _R = 0V, f = 1MHz

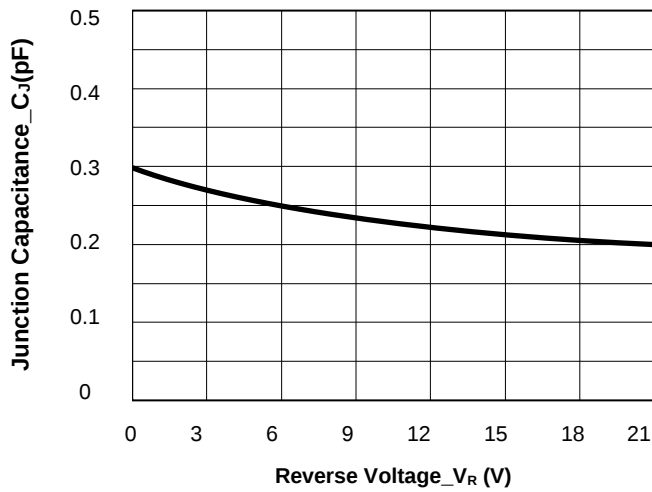
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Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

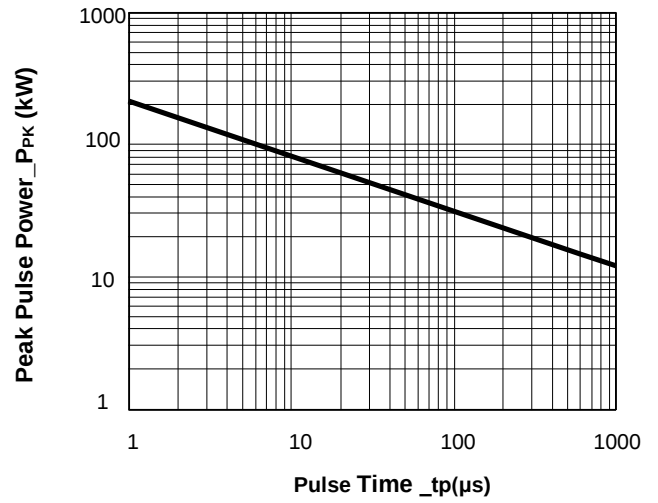


Definitions of electrical characteristics

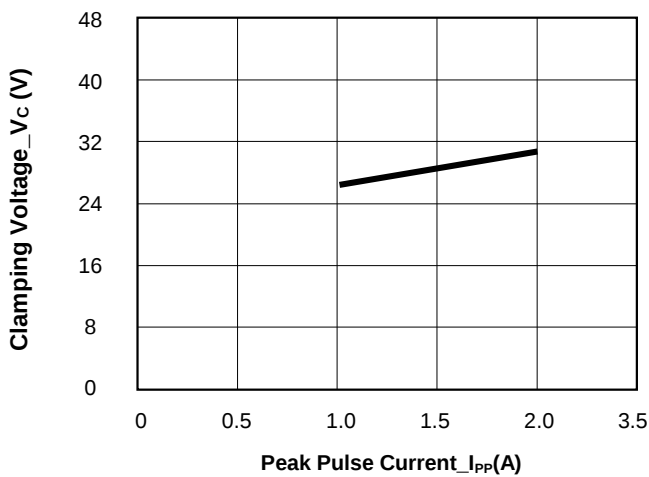
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



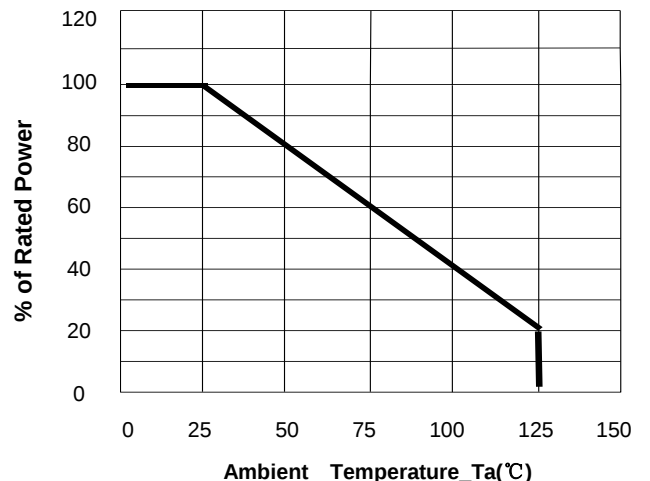
Junction Capacitance vs. Reverse Voltage



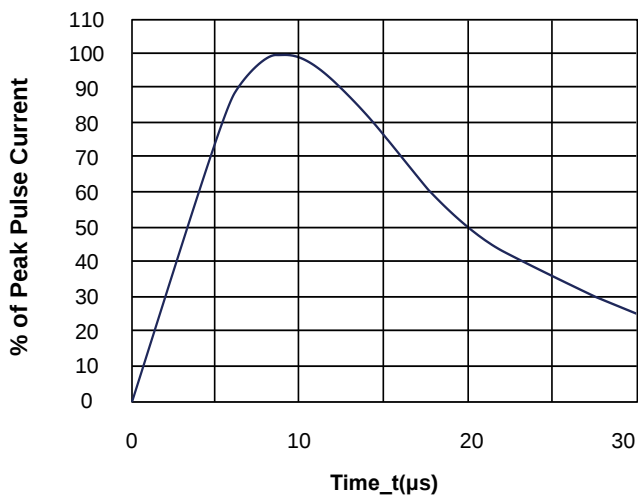
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

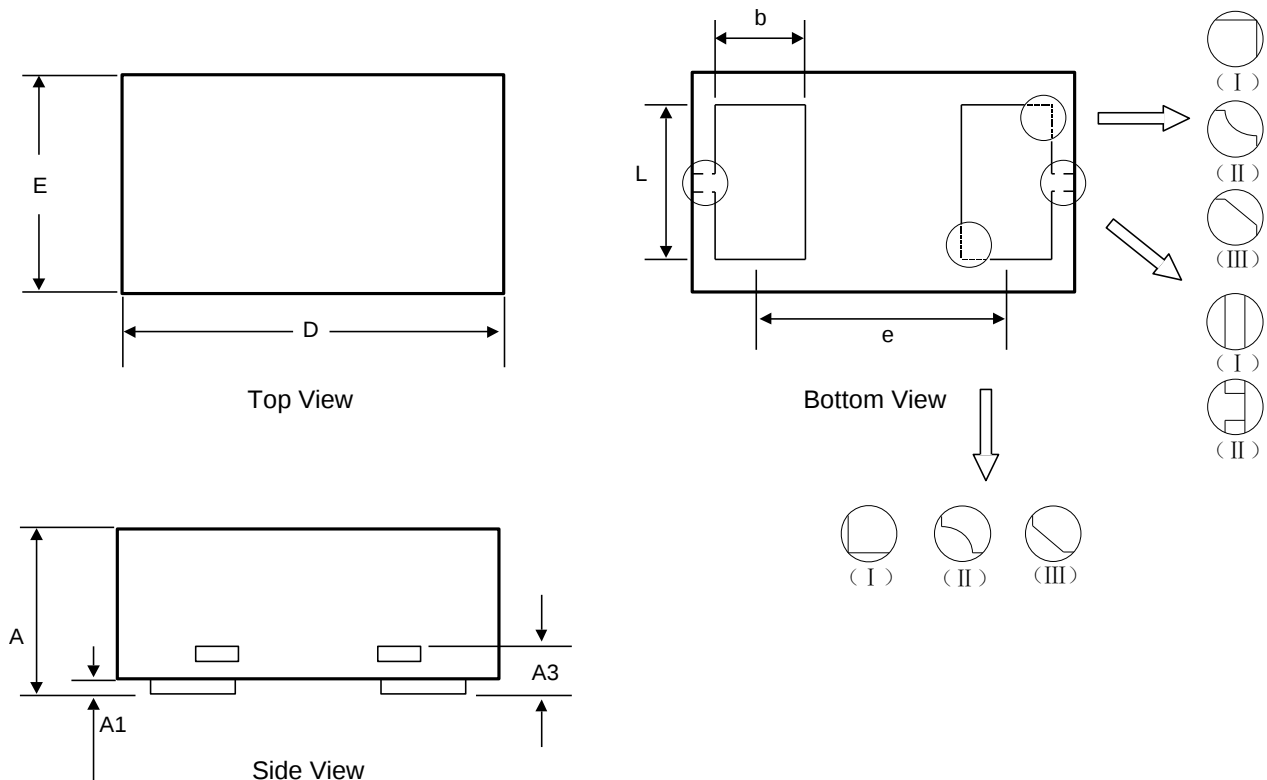


Power Derating Curve



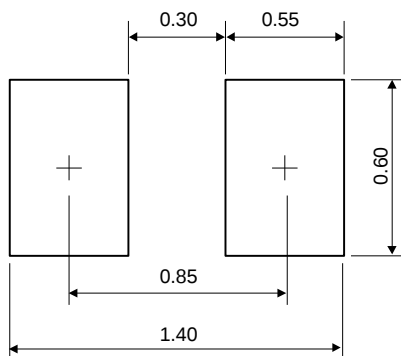
8/20μs Pulse Waveform

DFN1006-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.550
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)

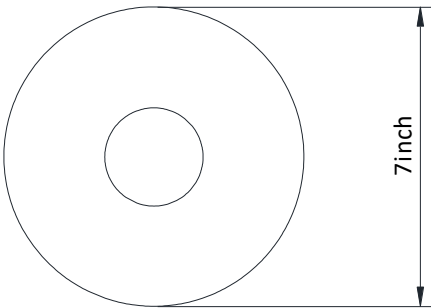


Notes:

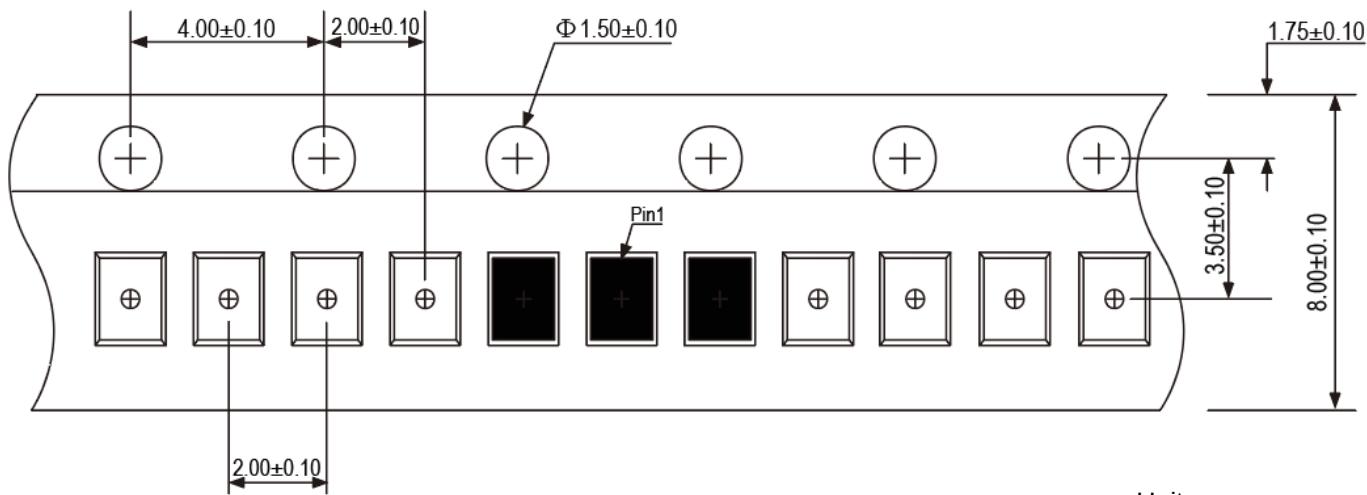
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

TAPE AND REEL INFORMATION

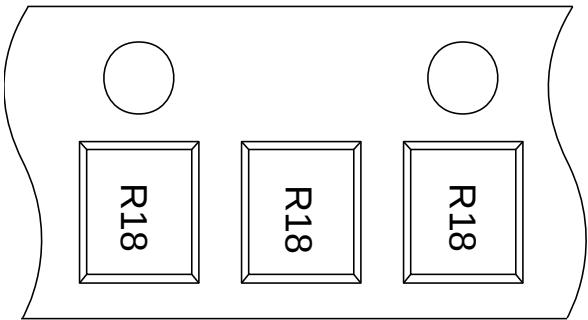
Reel Dimensions



Tape Dimensions



Unit:mm



User Direction of Feed

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